



KOREAN PATENT ABSTRACTS(KR)

Document Code:A

(11) Publication No.1020010066143 (43) Publication.Date. 20010711

(21) Application No.1019990067728 (22) Application Date. 19991231

(51) IPC Code:

H01L 21/66

(71) Applicant:

HYNIX SEMICONDUCTOR INC.

(72) Inventor:

PARK, JEONG RYEOL

(30) Priority:

(54) Title of Invention

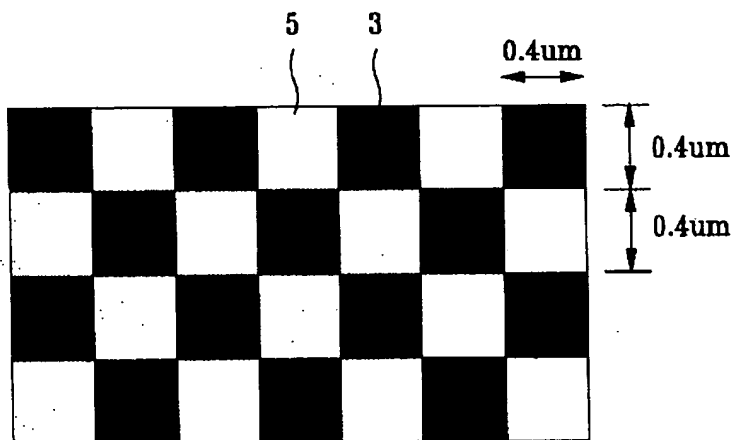
METHOD OF MEASURING DEPTH OF TRENCH OF SEMICONDUCTOR DEVICE

Representative drawing

(57) Abstract:

PURPOSE: A method of measuring a depth of a trench of a semiconductor device is to simply measure the depth of the trench using a nanospec device, thereby saving measuring time and fabricating cost.

CONSTITUTION: A trench(5) and an insulating layer(3) respectively having a length of 0.4 micrometer are alternately provided to form a pattern in the shape of a lattice. An indicating value of nanospec according to a depth of the trench, which is detected in a constant frequency band corresponding to a thickness of the insulating layer, is set. Then, laser beam is scanned on the pattern in the shape of a lattice using a nanospec device to detect the indicated value in the desired frequency band. Then, the indicated value is calculated in terms of thicknesses. A length of the pattern is 1 micrometer or less. The insulating layer is a nitride layer. Therefore, the depth of the trench is measured by monitoring the pattern in the shape of a lattice.



COPYRIGHT 2001 KIPO

if display of image is failed, press (F5)